TOSHIBA Photocoupler GaAs IRED & Photo−Transistor

TLP781, TLP781F

Office Equipment

Household Appliances

Solid State Relays

Switching Power Supplies

Various Controllers

Signal Transmission Between Different Voltage Circuits

The TOSHIBA TLP781 consists of a silicone photo−transistor optically coupled to a gallium arsenide infrared emitting diode in a four lead plastic DIP (DIP4) with having high isolation voltage (AC: 5kV$_{RMS}$ (min)).

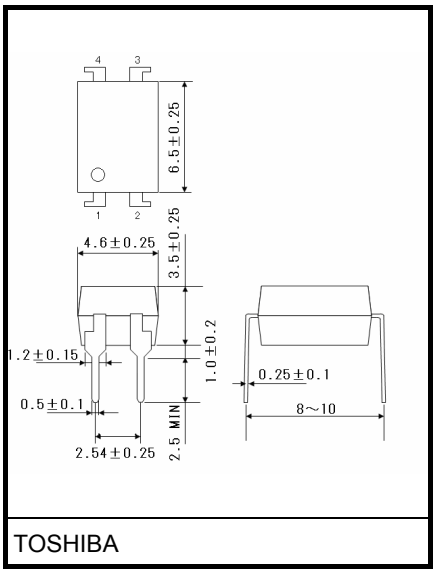
- TLP781 : 7.62mm pitch type DIP4
- TLP781F : 10.16mm pitch type DIP4
- Collector-emitter voltage: 80V (min.)
- Current transfer ratio: 50% (min.)
  Rank GB: 100% (min.)
- Isolation voltage: 5000V$_{rms}$ (min.)
- UL recognized: UL1577, file No. E67349
- BSI approved: BS EN60065:2002
  Approved no.8961
  BS EN60950-1:2006
  Approved no.8962
- SEMKO approval: EN60950-1,EN60065 under plan

- Option(D4)type
  VDE approved : DIN EN60747-5-2
  Certificate No. 40021173
  (Note): When an EN60747-5-2 approved type is needed,
  Please designate “Option (D4)”

- Construction mechanical rating

	7.62mm Pitch Standard Type	10.16mm Pitch TLPxxxF Type
Creepage distance	6.5mm(min)	8.0mm(min)
Clearance	6.5mm(min)	8.0mm(min)
Insulation thickness	0.4mm(min)	0.4mm(min)

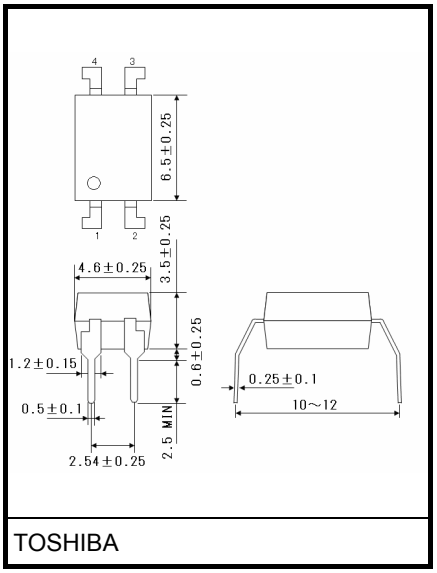
TLP781 Unit in mm



TOSHIBA

Weight: 0.25g (typ.)

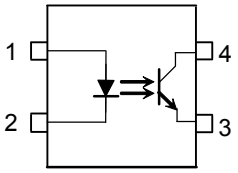
TLP781F Unit in mm



TOSHIBA

Weight: 0.25g (typ.)

Pin Configurations (top view)



1 : Anode
2 : Cathode
3 : Emitter
4 : Collector

Current Transfer Ratio

Type	Classification (Note 1)	Current Transfer Ratio (%) (I_C / I_F) I_F = 5mA, V_{CE} = 5V, Ta = 25°C		Marking Of Classification
		Min	Max	
TLP781	(None)	50	600	Blank, Y, Y+, YE,G, G+, B, B+,BL,GB
	Rank Y	50	150	YE
	Rank GR	100	300	GR
	Rank BL	200	600	BL
	Rank GB	100	600	GB
	Rank YH	75	150	Y+
	Rank GRL	100	200	G
	Rank GRH	150	300	G+
	Rank BLL	200	400	B

(Note 1): Ex. rank GB: TLP781 (GB)

(Note 2): Application type name for certification test, please use standard product type name, i. e. TLP781 (GB): TLP781

Absolute Maximum Ratings (Ta = 25°C)

	Characteristic		Symbol	Rating	Unit
LED	Forward current		I_F	60	mA
	Forward current derating(Ta ≥ 39°C)		ΔI_F / °C	−0.7	mA / °C
	Pulse forward current	(Note 3)	I_{FP}	1	A
	Power dissipation		P_D	100	mW
	Power dissipation derating		ΔP_D / °C	−1.0	mW / °C
	Reverse voltage		V_R	5	V
	Junction temperature		T_j	125	°C
Detector	Collector−emitter voltage		V_{CEO}	80	V
	Emitter−collector voltage		V_{ECO}	7	V
	Collector current		I_C	50	mA
	Power dissipation(single circuit)		P_C	150	mW
	Power dissipation derating (Ta ≥ 25°C)(single circuit)		ΔP_C / °C	−1.5	mW / °C
	Junction temperature		T_j	125	°C
Operating temperature range			T_{opr}	−55~110	°C
Storage temperature range			T_{stg}	−55~125	°C
Lead soldering temperature (10s)			T_{sol}	260	°C
Total package power dissipation			P_T	250	mW
Total package power dissipation derating (Ta ≥ 25°C)			ΔP_T / °C	−2.5	mW / °C
Isolation voltage		(Note 4)	BV_S	5000	V_{rms}

(Note): Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 3): 100μs pulse, 100Hz frequency

(Note 4): AC, 1 min., R.H.≤ 60%. Apply voltage to LED pin and detector pin together.

Recommended Operating Conditions

Characteristic	Symbol	Min	Typ.	Max	Unit
Supply voltage	V_{CC}	—	5	24	V
Forward current	I_F	—	16	25	mA
Collector current	I_C	—	1	10	mA
Operating temperature	T_{opr}	−25	—	85	°C

(Note): Recommended operating conditions are given as a design guideline to obtain expected performance of the device.
Additionally, each item is an independent guideline respectively.
In developing designs using this product, please confirm specified characteristics shown in this document.

Individual Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
LED	Forward voltage	V_F	I_F = 10 mA	1.0	1.15	1.3	V
	Reverse current	I_R	V_R = 5 V	—	—	10	μA
	Capacitance	C_T	V = 0, f = 1 MHz	—	30	—	pF
Detector	Collector−emitter breakdown voltage	$V_{(BR)\ CEO}$	I_C = 0.5 mA	80	—	—	V
	Emitter−collector breakdown voltage	$V_{(BR)\ ECO}$	I_E = 0.1 mA	7	—	—	V
	Collector dark current	$I_D(I_{CEO})$	V_{CE} = 24 V	—	0.01	0.1	μA
			V_{CE} = 24 V, Ta = 85°C	—	0.6	50	μA
	Capacitance (collector to emitter)	C_{CE}	V = 0, f = 1 MHz	—	10	—	pF

Coupled Electrical Characteristics (Ta = 25°C)

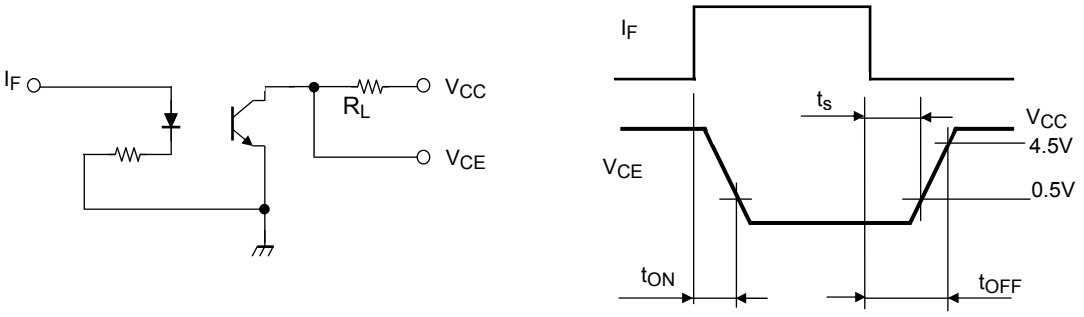
Characteristic	Symbol	Test Condition		Min	Typ.	Max	Unit
Current transfer ratio	I_C / I_F	I_F = 5 mA, V_{CE} = 5 V		50	—	600	%
			Rank GB	100	—	600	
Saturated CTR	I_C / $I_{F\ (sat)}$	IF = 1 mA, V_{CE} = 0.4 V		—	60	—	%
			Rank GB	30	—	—	
Collector−emitter saturation voltage	$V_{CE\ (sat)}$	I_C = 2.4 mA, I_F = 8 mA		—	—	0.4	V
		I_C = 0.2 mA, I_F = 1 mA		—	0.2	—	
			Rank GB	—	—	0.4	

Isolation Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Capacitance (input to output)	C_S	V_S = 0, f = 1 MHz	—	0.8	—	pF
Isolation resistance	R_S	V_S = 500 V	1×10^{12}	10^{14}	—	Ω
Isolation voltage	BV_S	AC, 1 minute	5000	—	—	V_{rms}
		AC, 1 second, in oil	—	10000	—	
		DC, 1 minute, in oil	—	10000	—	Vdc

Switching Characteristics (Ta = 25°C)

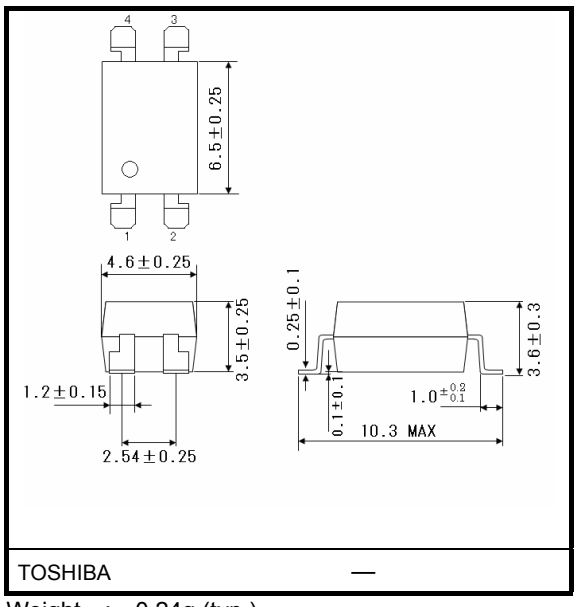
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Rise time	t_r	V_{CC} = 10 V, I_C = 2 mA R_L = 100Ω	—	2	—	μs
Fall time	t_f		—	3	—	
Turn−on time	t_{on}		—	3	—	
Turn−off time	t_{off}		—	3	—	
Turn−on time	t_{ON}	R_L = 1.9 kΩ (Note 5) V_{CC} = 5 V, I_F = 16 mA	—	2	—	μs
Storage time	t_s		—	25	—	
Turn−off time	t_{OFF}		—	50	—	



(Note 5): Switching time test circuit

Surface-Mount Lead Form Options

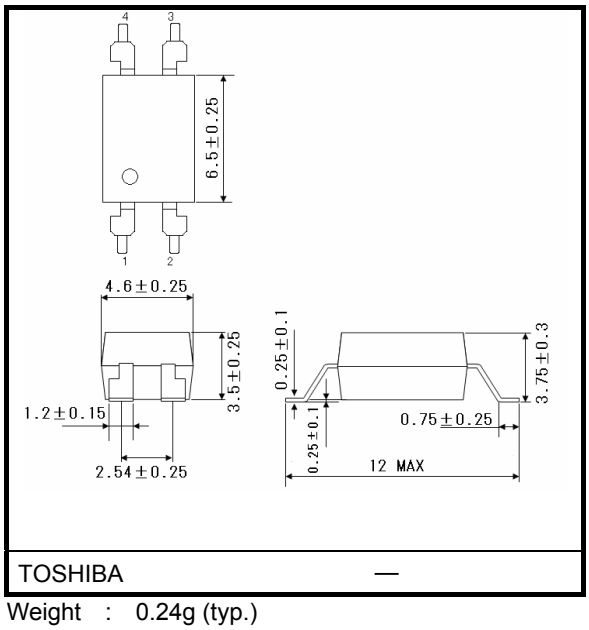
TLP781(LF6) Unit in mm



TOSHIBA	—

Weight : 0.24g (typ.)

TLP781F(LF7) Unit in mm



TOSHIBA	—

Weight : 0.24g (typ.)

Specifications for Embossed-Tape Packing: (TP6), (TP7)

1. Applicable Package

Package Name	Product Type
DIP4LF6	TLP781
DIP4LF7	TLP781F

2. Product Naming System

Type of package used for shipment is denoted by a symbol suffix after a product number. The method of classification is as below.

(Example 1)

TLP781 (BL－TP6)

- Tape type
- CTR rank
- Device name

(Example 2)

TLP781F (BL－TP7)

- Tape type
- CTR rank
- Device name

3. Tape Dimensions

3.1 Orientation of Device in Relation to Direction of Tape Movement

Device orientation in the recesses is as shown in Figure 1.

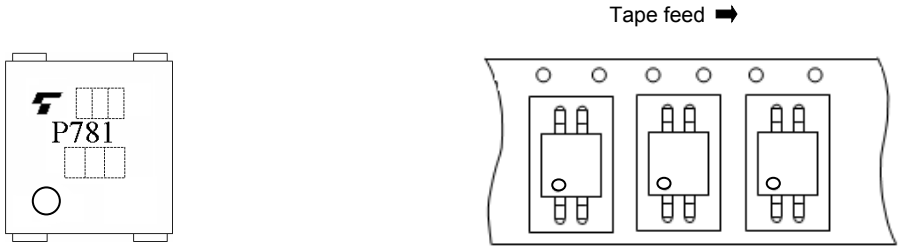


Figure1 Device Orientation

3.2 Tape Packing Quantity:2000 devices per reel

3.3 Empty Device Recesses Are as Shown in Table 1.

Table1 Empty Device Recesses

	Standard	Remarks
Occurrences of 2 or more successive empty device recesses	0	Within any given 40-mm section of tape, not including leader and trailer
Single empty device recesses	6 devices (max.) per reel	Not including leader and trailer

3.4 Start and End of Tape

The start of the tape has 30 or more empty holes. The end of the tape has 50 or more empty holes.

3.5 Tape Specification

[1] TLP781 (TP6)

(1)Tape material: Plastic

(2)Dimensions: The tape dimensions are as shown in Figure 2.

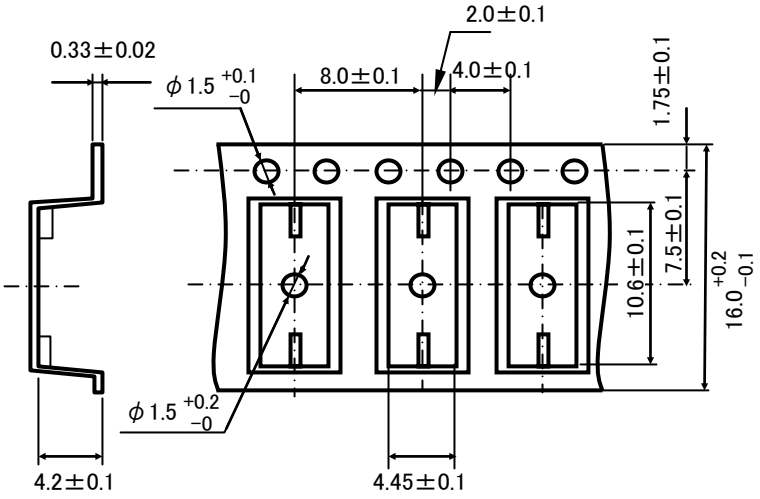


Figure 2 Tape Forms

[2] TLP781F (TP7)

(1)Tape material: Plastic

(2)Dimensions: The tape dimensions are as shown in Figure 3.

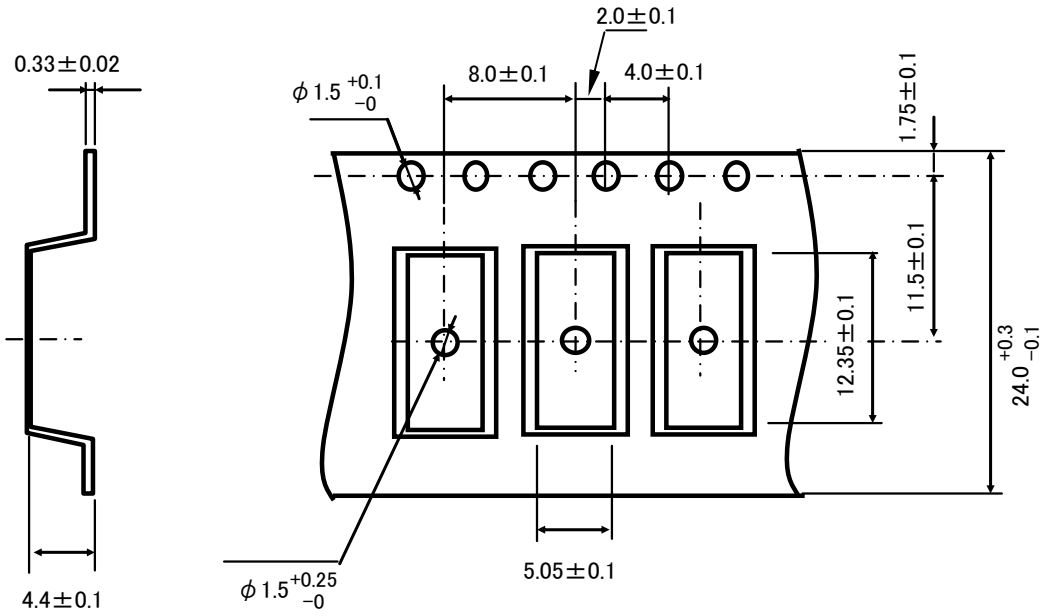


Figure 3 Tape Forms

3.6 Reel Specification

[1] TLP781 (TP6)

(1)Material: Plastic

(2)Dimensions: The reel dimensions are as shown in Figure 4.

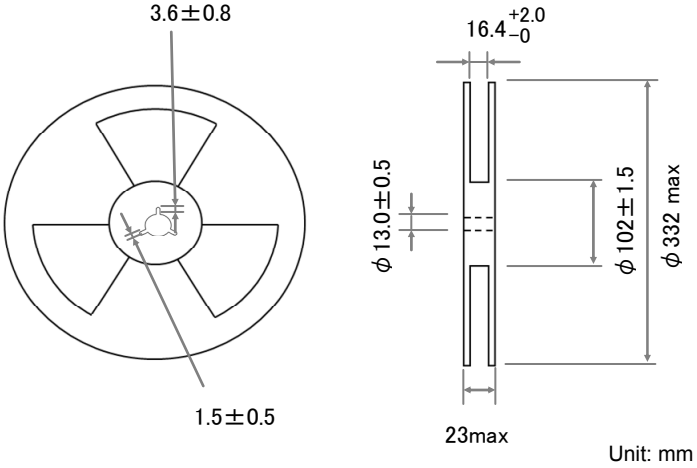


Figure 4 Reel Forms

[2] TLP781F (TP7)

(1)Material: Plastic

(2)Dimensions: The reel dimensions are as shown in Figure 5.

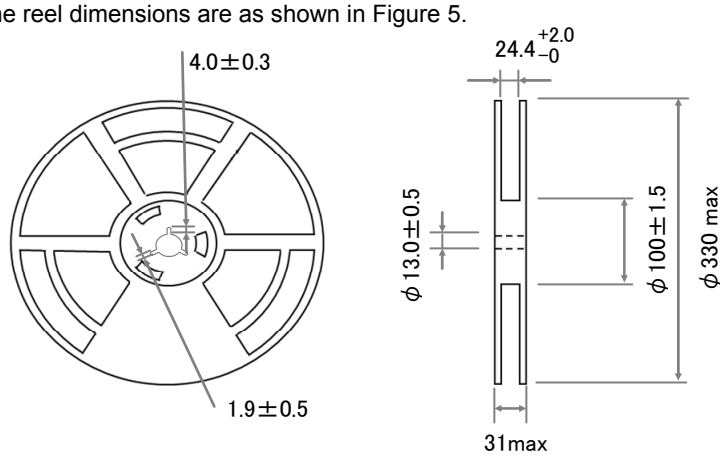


Figure 5 Reel Forms

4. Packing

One reel of photocouplers is packed in a shipping carton.

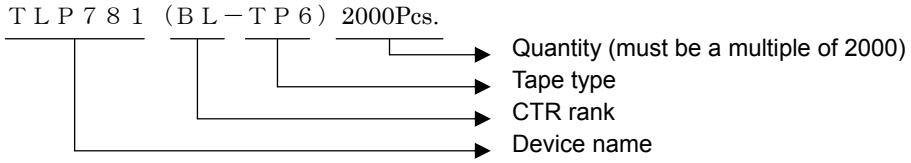
5. Label Indication

The carton bears a label indicating the product number, the symbol representing classification of standard, the quantity, the lot number and the Toshiba company name.

6. Ordering Information

When placing an order, please specify the product number, the CTR rank, the tape type and the quantity as shown in the following example.

(Example)



(Note): The order code may be suffixed with wither a letter or a digit.

Please contact your nearest Toshiba sales representative for more details.

Soldering and Storage

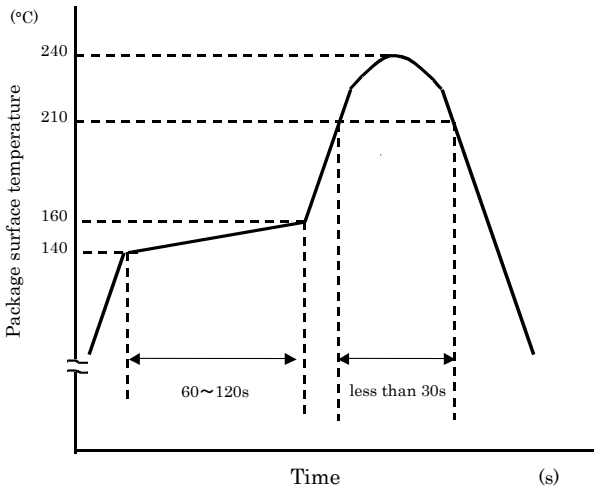
1. Soldering

1.1 Soldering

When using a soldering iron or medium infrared ray/hot air reflow, avoid a rise in device temperature as much as possible by observing the following conditions.

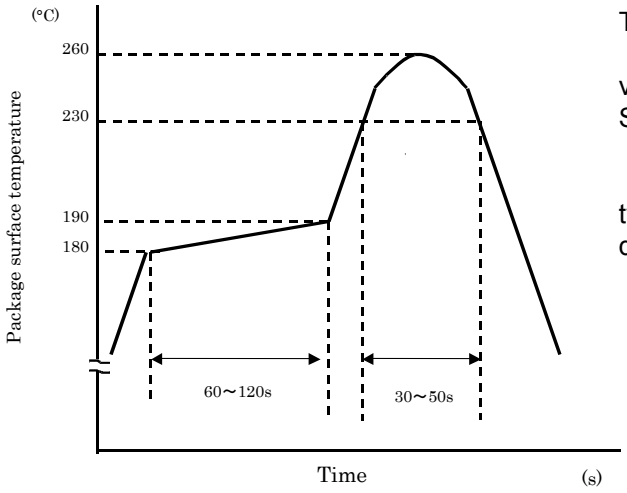
1) Using solder reflow

·Temperature profile example of lead (Pb) solder



This profile is based on the device's maximum heat resistance guaranteed value.
Set the preheat temperature/heating temperature to the optimum temperature corresponding to the solder paste type used by the customer within the described profile.

·Temperature profile example of using lead (Pb)-free solder



This profile is based on the device's maximum heat resistance guaranteed value.
Set the preheat temperature/heating temperature to the optimum temperature corresponding to the solder paste type used by the customer within the described profile.

2) Using solder flow (for lead (Pb) solder, or lead (Pb)-free solder)

・Please preheat it at 150°C between 60 and 120 seconds.

・Complete soldering within 10 seconds below 260°C. Each pin may be heated at most once.

3) Using a soldering iron

Complete soldering within 10 seconds below 260°C, or within 3 seconds at 350°C. Each pin may be heated at most once.